



**CHENMKO ENTERPRISE CO.,LTD**

**SURFACE MOUNT**

SCHOTTKY BARRIER DIODE

VOLTAGE 40 Volts CURRENT 30 mAmpere

Halogens free devices

**CH751VDWGP**

**APPLICATION**

- \* High speed switching for detection

**FEATURE**

- \* Small surface mounting type. (SOT-563)
- \* Low VF and low IR
- \* High reliability

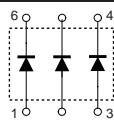
**CONSTRUCTION**

- \* Silicon epitaxial planar

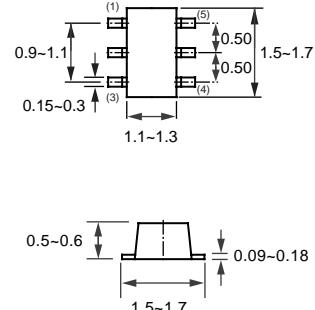
**MARKING**

- \* JV

**CIRCUIT**



**SOT-563**



Dimensions in millimeters

**SOT-563**

**MAXIMUM RATINGS ( At TA = 25°C unless otherwise noted )**

RATINGS	SYMBOL	CH751VDWGP	UNITS
Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	40	Volts
Maximum RMS Voltage	V <sub>RMS</sub>	28	Volts
Maximum DC Blocking Voltage	V <sub>Dc</sub>	40	Volts
Maximum Average Forward Rectified Current	I <sub>O</sub>	30	mAmps
Peak Forward Surge Current at 8.3 mSec single half sine-wave	I <sub>FSM</sub>	0.2	Amps
Typical Junction Capacitance between Terminal (Note 1)	C <sub>J</sub>	2.0	pF
Maximum Operating Temperature Range	T <sub>J</sub>	+125	°C
Storage Temperature Range	T <sub>STG</sub>	-40 to +125	°C

**ELECTRICAL CHARACTERISTICS ( At TA = 25°C unless otherwise noted )**

CHARACTERISTICS	SYMBOL	CH751VDWGP	UNITS
Maximum Instantaneous Forward Voltage at I <sub>F</sub> = 1mA	V <sub>F</sub>	0.37	Volts
Maximum Average Reverse Current at V <sub>R</sub> = 30V	I <sub>R</sub>	0.5	uAmps

NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 1.0 volts.  
2. ESD sensitive product handling required.

2007-3

## RATING CHARACTERISTIC CURVES ( CH751VDWGP )

FIG. 1 - FORWARD CHARACTERISTICS

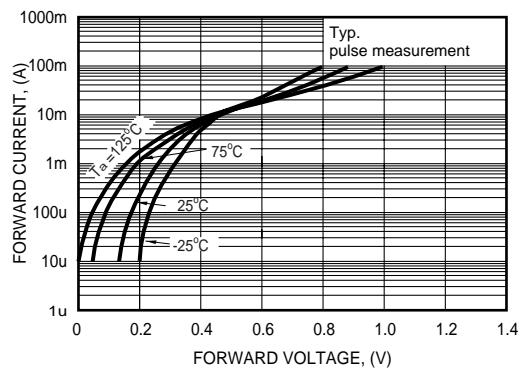


FIG. 2 - REVERSE CHARACTERISTICS

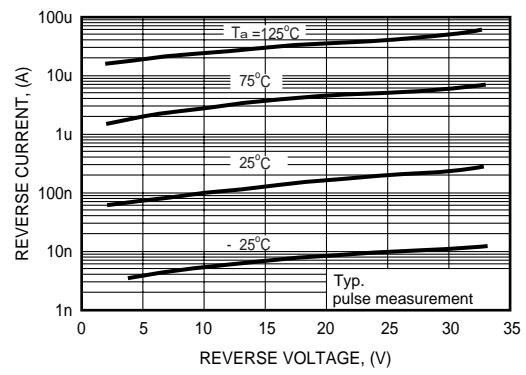


FIG. 3 - TYPICAL JUNCTION CAPACITANCE

